



# Hydrogen Plasma Photoresist Strip And Polymeric Residue Cleanup Process For Low Dielectric Constant Materials

## ABSTRACT OF THE DISCLOSURE

A method (100) of fabricating an electronic device (200) formed on a semiconductor wafer. The method forms a layer (215) of a first material in a fixed position relative to the wafer. The first material has a dielectric constant less than 3.6. The method also forms a photoresist layer in (216) a fixed position relative to the layer of the first material. The method also forms at least one void (220) through the layer of the first material in response to the photoresist layer. Further, the method subjects (106) the semiconductor wafer to a plasma which incorporates a gas which includes hydrogen so as to remove the photoresist layer.